IN THE CLAIMS

This listing of claims replaces all prior listings:

1. (Previously Presented) A method of manufacturing a semiconductor device including a laser chip and a base having the laser chip mounted thereon, including the step of:

providing an assembly with the laser chip mounted on the base, the assembly including a wire-bonded wiring; and

after bonding the wire-bonded wire, irradiating the laser chip and base with an energy beam having a shorter wavelength than an oscillation wavelength of the laser chip to remove adherent from the laser chip and the base.

2. (Previously Presented) A method of manufacturing a semiconductor device according to claim 1 including the step of:

sealing the base from the outside, after the step of irradiating the laser chip and the base with the energy beam.

3. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein a laser chip having a nitride semiconductor layer is used as the laser chip.

4. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein a laser chip having an oscillation wavelength of 550 nm or less is used as the laser chip.

5. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein irradiation takes place using laser light or ultraviolet light as the energy beam.

6. (Previously Presented) A method of manufacturing a semiconductor device including a laser chip, a base, and a wire-bonded wire, the method including the step of:

after bonding the wire-bonded wire, irradiating the base having the laser chip mounted thereon with plasma.

7. (Previously Presented) A method of manufacturing a semiconductor device according to claim 6 including the step of:

sealing the base from the outside, after the step of irradiating the base with the plasma.

8. (Original) A method of manufacturing a semiconductor device according to claim 6, wherein a laser chip having a nitride semiconductor layer is used as the laser chip.

9. (Original) A method of manufacturing a semiconductor device according to claim 6, wherein a laser chip having an oscillation wavelength of 550 nm or less is used as the laser chip.

10. (Original) A method of manufacturing a semiconductor device according to claim 6, wherein the step of irradiating the base with the plasma takes place in an atmosphere of oxygen.